

Notice of References CitedApplicant/Patent
Takemura et al.Application/Control No.
09/321,715Examiner
M. WilczewskiArt Unit
2822

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U.S. PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Name	Classification ²	
A	4,597,160	7/1986	Ipri	438	166
B	4,851,363	7/1989	Troxell et al.	----	----
C					
D					
E					
F					
G					
H					
I					
J					
K					
L					
M					

FOREIGN PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Country	Name	Classification ²	
N						
O						
P						
Q						
R						
S						
T						

NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Katz et al., "Defect Formation During High-Pressure, Low-Temperature Steam Oxidation of Silicon", Journal of the Electrochem. Soc., Vol. 125, No. 10, pp. 1680-1683.
V	Ligenza, "Oxidation of Silicon by High-Pressure Steam", Journal of the Electrochem. Soc., Vol. 109, No. 2, February 1962, pp. 73-76.
W	Wolf et al., Silicon Processing for the VLSI Era, Volume 1-Process Technology; Lattice Press, 1986, pp. 171-175.
X	

* A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).

¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.